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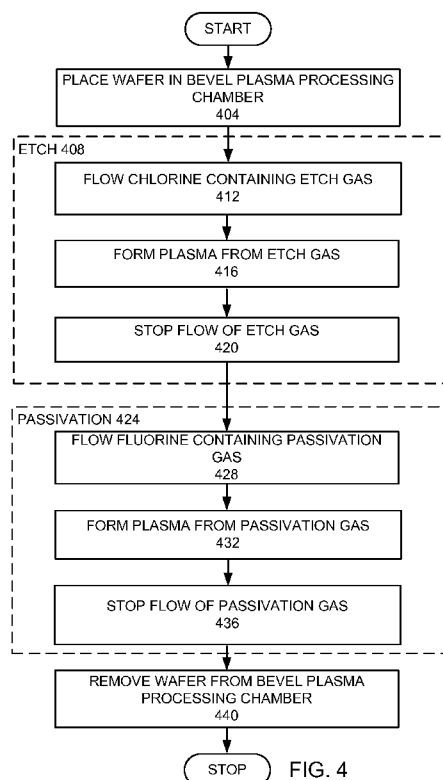
(54) **Title:** HIGH PRESSURE BEVEL ETCH PROCESS

FIG. 4

(57) **Abstract:** A method of bevel edge processing a semiconductor in a bevel plasma processing chamber in which the semiconductor substrate is supported on a semiconductor substrate support is provided. The method comprises evacuating the bevel etcher to a pressure of 3 to 100 Torr and maintaining RF voltage under a threshold value; flowing a process gas into the bevel plasma processing chamber; energizing the process gas into a plasma at a periphery of the semiconductor substrate; and bevel processing the semiconductor substrate with the plasma.



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— *as to the applicant's entitlement to claim the priority of
the earlier application (Rule 4.17(iii))*